

ABSTRACT OF THE DISCLOSURE

There is disclosed a semiconductor light emitting element formed by selective growth and being high in light emitting efficiency, in which at least one GaN-based layer grown by ELO is stacked/formed on a sapphire substrate, and a fluorescent substance for converting an ultraviolet light to a visible light is contained in a selective growth mask material layer for use in this case. Since this fluorescent substance converts the ultraviolet light to the visible light, a binding efficiency of the ultraviolet light to the fluorescent substance is enhanced in either one of a center light emitting type and UV light emitting type of light emitting elements. By further containing the fluorescent substance into a passivation film, the efficiency is further enhanced.